

ABSTRACT OF THE DISCLOSURE

Disclosed are an electrode of a semiconductor device and a method of forming the
5 same. A polysilicon layer is formed on a semiconductor substrate. An amorphous silicon
capping layer is then formed on the polysilicon layer. A silicide layer is formed on the
capping layer. The capping layer prevents chlorine ions from diffusing downward to the
polysilicon layer. Accordingly, abnormal growth of the polysilicon layer can be
prevented, thus improving the stability of the electrical characteristics of a semiconductor
10 device electrode.